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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not Yet Assigned
				Filing Date	Concurrently Herewith
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	1	of	10	Attorney Docket Number	M4065.0635/P635 A

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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NON PATENT LITERATURE DOCUMENTS				
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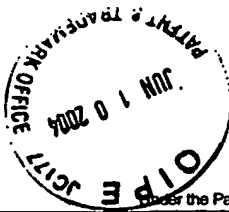
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Sheet	1	of	3

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				Application Number	10/800,707
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	March 16, 2004
				First Named Inventor	Kristy A. Campbell
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0635/P635
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K. Picerno

7/13/05